

## High Speed Infrared Emitting Diode, 850 nm, GaAlAs Double Hetero



94 8389


**FEATURES**

- Package type: leaded
- Package form: T-1 $\frac{3}{4}$
- Dimensions (in mm):  $\varnothing$  5
- Peak wavelength:  $\lambda_p = 850$  nm
- High reliability
- High radiant power
- High radiant intensity
- Angle of half intensity:  $\varphi = \pm 10^\circ$
- Low forward voltage
- Suitable for high pulse current operation
- High modulation bandwidth:  $f_c = 18$  MHz
- Good spectral matching with CMOS cameras
- Compliant to RoHS Directive 2002/95/EC and in accordance to WEEE 2002/96/EC

**DESCRIPTION**

TSHG6210 is an infrared, 850 nm emitting diode in GaAlAs double hetero (DH) technology with high radiant power and high speed, molded in a clear, untinted plastic package.

**APPLICATIONS**

- Infrared radiation source for operation with CMOS cameras
- High speed IR data transmission
- Smoke-automatic fire detectors

**PRODUCT SUMMARY**

COMPONENT	$I_e$ (mW/sr)	$\varphi$ (deg)	$\lambda_p$ (nm)	$t_r$ (ns)
TSHG6210	230	$\pm 10$	850	20

**Note**

- Test conditions see table "Basic Characteristics"

**ORDERING INFORMATION**

ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
TSHG6210	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1 $\frac{3}{4}$

**Note**

- MOQ: minimum order quantity

**ABSOLUTE MAXIMUM RATINGS** ( $T_{amb} = 25^\circ\text{C}$ , unless otherwise specified)

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		$V_R$	5	V
Forward current		$I_F$	100	mA
Peak forward current	$t_p/T = 0.5$ , $t_p = 100 \mu\text{s}$	$I_{FM}$	200	mA
Surge forward current	$t_p = 100 \mu\text{s}$	$I_{FSM}$	1	A
Power dissipation		$P_V$	180	mW
Junction temperature		$T_j$	100	$^\circ\text{C}$
Operating temperature range		$T_{amb}$	- 40 to + 85	$^\circ\text{C}$
Storage temperature range		$T_{stg}$	- 40 to + 100	$^\circ\text{C}$
Soldering temperature	$t \leq 5$ s, 2 mm from case	$T_{sd}$	260	$^\circ\text{C}$
Thermal resistance junction/ambient	J-STD-051, leads 7 mm, soldered on PCB	$R_{thJA}$	230	K/W

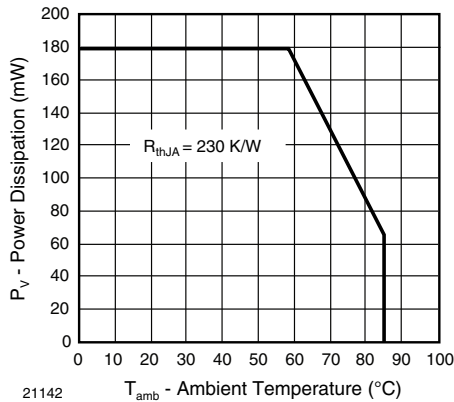


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

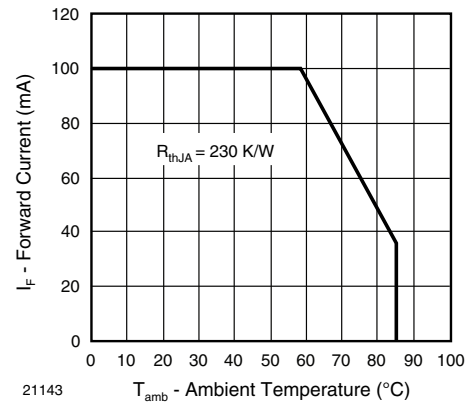


Fig. 2 - Forward Current Limit vs. Ambient Temperature

<b>BASIC CHARACTERISTICS</b> (T <sub>amb</sub> = 25 °C, unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	I <sub>F</sub> = 100 mA, t <sub>p</sub> = 20 ms	V <sub>F</sub>		1.5	1.8	V
	I <sub>F</sub> = 1 A, t <sub>p</sub> = 100 μs	V <sub>F</sub>		2.3		V
Temperature coefficient of V <sub>F</sub>	I <sub>F</sub> = 1 mA	TK <sub>V<sub>F</sub></sub>		- 1.8		mV/K
Reverse current	V <sub>R</sub> = 5 V	I <sub>R</sub>			10	μA
Junction capacitance	V <sub>R</sub> = 0 V, f = 1 MHz, E = 0	C <sub>j</sub>		125		pF
Radiant intensity	I <sub>F</sub> = 100 mA, t <sub>p</sub> = 20 ms	I <sub>e</sub>	140	230	420	mW/sr
	I <sub>F</sub> = 1 A, t <sub>p</sub> = 100 μs	I <sub>e</sub>		2300		mW/sr
Radiant power	I <sub>F</sub> = 100 mA, t <sub>p</sub> = 20 ms	φ <sub>e</sub>		55		mW
Temperature coefficient of φ <sub>e</sub>	I <sub>F</sub> = 100 mA	TK <sub>φ<sub>e</sub></sub>		- 0.35		%/K
Angle of half intensity		φ		± 10		deg
Peak wavelength	I <sub>F</sub> = 100 mA	λ <sub>p</sub>	820	850	880	nm
Spectral bandwidth	I <sub>F</sub> = 100 mA	Δλ		40		nm
Temperature coefficient of λ <sub>p</sub>	I <sub>F</sub> = 100 mA	TKλ <sub>p</sub>		0.25		nm/K
Rise time	I <sub>F</sub> = 100 mA	t <sub>r</sub>		20		ns
Fall time	I <sub>F</sub> = 100 mA	t <sub>f</sub>		13		ns
Cut-off frequency	I <sub>DC</sub> = 70 mA, I <sub>AC</sub> = 30 mA pp	f <sub>c</sub>		18		MHz
Virtual source diameter		d		3.7		mm

**BASIC CHARACTERISTICS** ( $T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified)

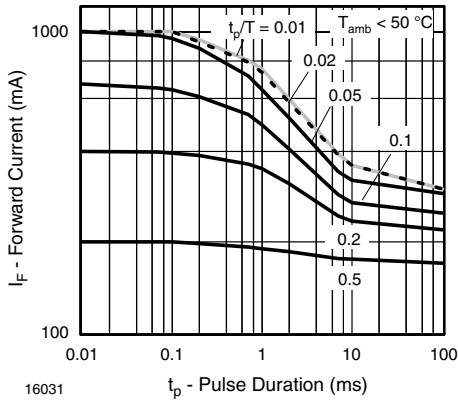


Fig. 3 - Pulse Forward Current vs. Pulse Duration

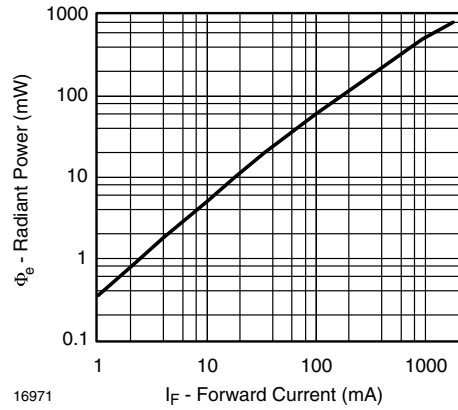


Fig. 6 - Radiant Power vs. Forward Current

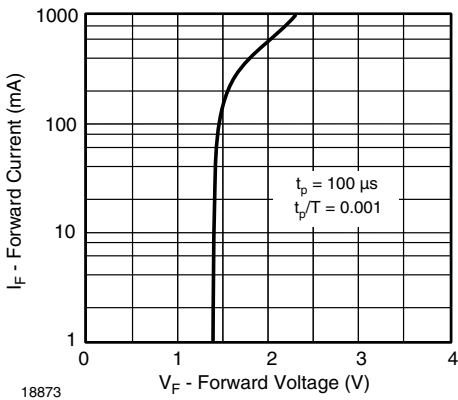


Fig. 4 - Forward Current vs. Forward Voltage

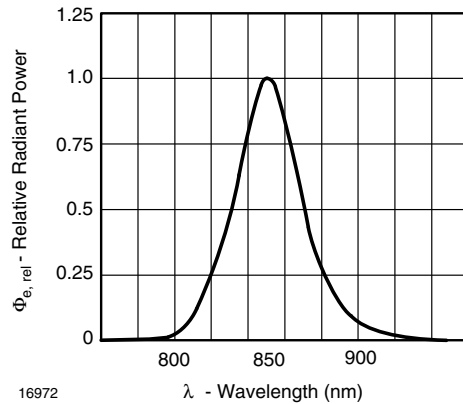


Fig. 7 - Relative Radiant Power vs. Wavelength

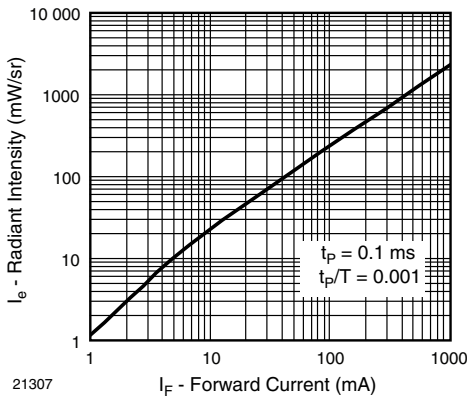


Fig. 5 - Radiant Intensity vs. Forward Current

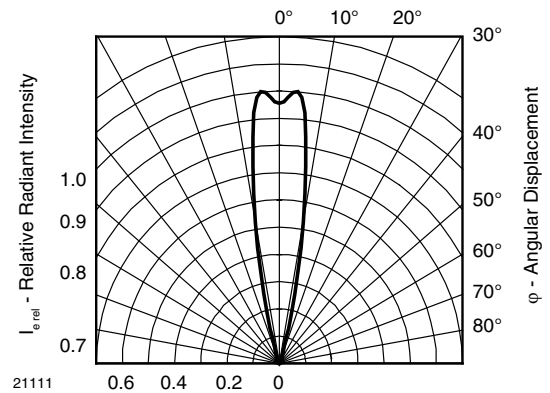
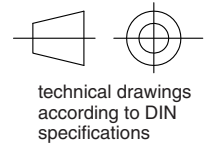
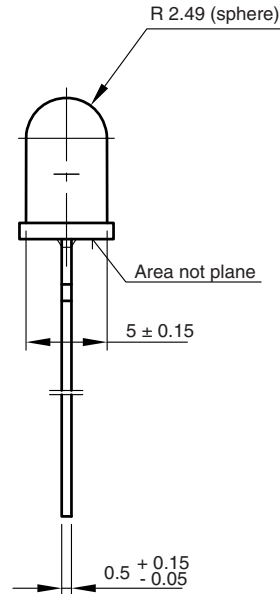
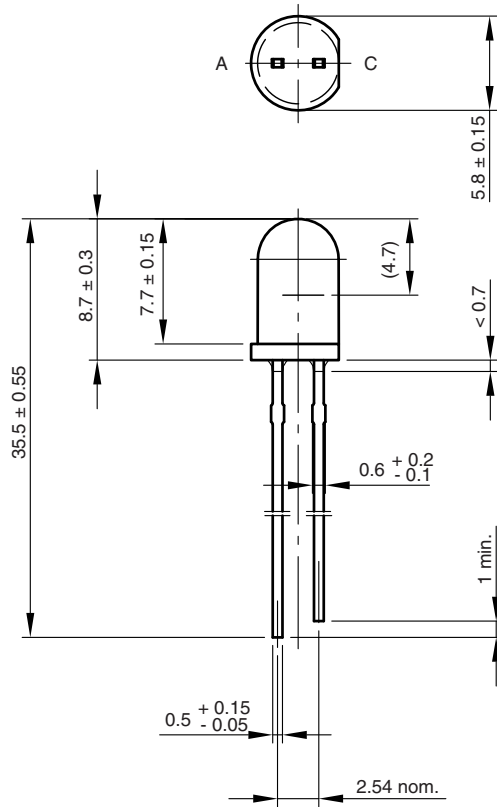


Fig. 8 - Relative Radiant Intensity vs. Angular Displacement



**PACKAGE DIMENSIONS** in millimeters



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